

## 60V N-Channel MOSFET



**SOT-363** 

#### Pin Definition:

1. Source 2 6. Drain 2 2. Gate 2

5. Gate 1 4. Source 1

3. Drain 1

#### PRODUCT SUMMARY

V <sub>DS</sub> (V)	$R_{DS(on)}(m\Omega)$	I <sub>D</sub> (A)
	2 @ V <sub>GS</sub> = 10V	300
60	4 @ V <sub>GS</sub> = 4.5V	200

## **Features**

- Low On-Resistance
- **ESD Protection**
- High Speed Switching
- Low Voltage Drive

## **Ordering Information**

Part No.	Package	Packing
TSM2N7002KDCU6 RFG	SOT-363	3Kpcs / 7" Reel

Note: "G" denote for Halogen Free Product

# D2

**Block Diagram** 

**Dual N-Channel MOSFET** 

S2

## **Absolute Maximum Rating** (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage		V <sub>DS</sub>	60	V	
Gate-Source Voltage		$V_{GS}$	±20	V	
Drain Current	Continuous @ T <sub>A</sub> =25°C	I <sub>D</sub>	300	mA	
	Pulsed	I <sub>DM</sub>	800		
Drain Reverse Current	Continuous @ T <sub>A</sub> =25°C	I <sub>DR</sub>	300	mA	
	Pulsed	I <sub>DMR</sub>	800		
Maximum Power Dissipation		P <sub>D</sub>	300	mW	
Operating Junction Temperature		T <sub>J</sub>	+150	°C	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

## **Thermal Performance**

Parameter	Symbol	Limit	Unit
Lead Temperature (1/8" from case)	TL	5	S
Junction to Ambient Thermal Resistance (PCB mounted)	R⊖ <sub>JA</sub>	625	°C/W

#### Notes:

- a. Pulse width ≤300us, Duty cycle ≤2%
- b. When the device is mounted on a glass epoxy board with area measuring 1 x 0.75 x 0.62 inch.
- c. The power dissipation of the package may result in a continuous drain current.



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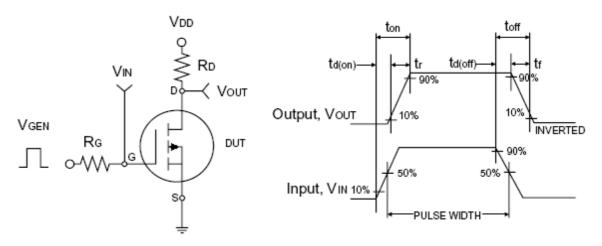


## **Electrical Specifications** (Ta = 25°C, unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	BV <sub>DSS</sub>	60			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	1.0	1.5	2.5	V
Gate Body Leakage	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$	I <sub>GSS</sub>			±10	uA
Zero Gate Voltage Drain Current	$V_{DS} = 60 \text{V}, V_{GS} = 0 \text{V}$	I <sub>DSS</sub>	1		1.0	uA
Drain Course On State Besistance	$V_{GS} = 10V, I_D = 300mA$	D	1	1.2	2	
Drain-Source On-State Resistance	Orain-Source On-State Resistance $V_{GS} = 4.5V, I_D = 100 \text{mA}$		1	2	4	Ω
Forward Transconductance	$V_{DS} = 10V, I_{D} = 200 \text{mA}$	9 <sub>fs</sub>	100			mS
Diode Forward Voltage	$I_S = 300 \text{mA}, V_{GS} = 0 \text{V}$	$V_{SD}$	1	0.8	1.4	V
Dynamic <sup>b</sup>						
Total Gate Charge	$V_{DS} = 10V, I_D = 250 \text{mA},$ $V_{GS} = 4.5 \text{V}$	$Q_g$	1	0.4	0.6	nC
Input Capacitance	\/ O5\/ \/ O\/	C <sub>iss</sub>	1	30		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C <sub>oss</sub>	1	6		pF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>	1	2.5		
Switching <sup>c</sup>						
Turn-On Delay Time	$V_{DD} = 30V, R_G = 10\Omega$	t <sub>d(on)</sub>	-		25	~ C
Turn-Off Delay Time	$I_D = 200 \text{mA}, V_{GEN} = 10 \text{V},$	t <sub>d(off)</sub>			35	nS

#### Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



**Switching Test Circuit** 

Switchin Waveforms

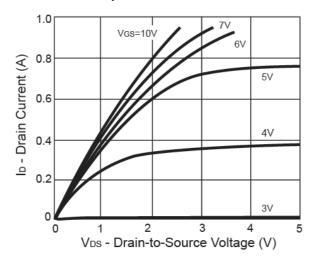


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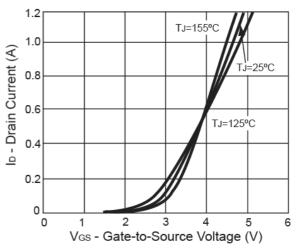


## Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

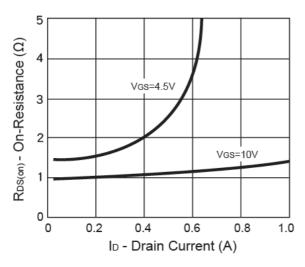
#### **Output Characteristics**



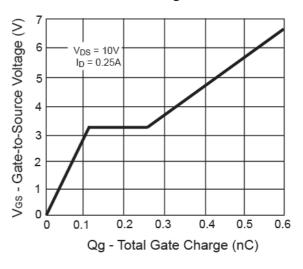
## Transfer Characteristics



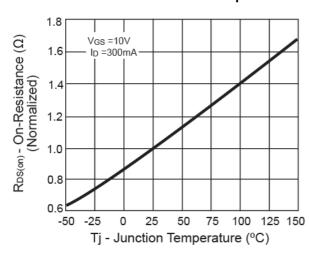
#### **On-Resistance vs. Drain Current**



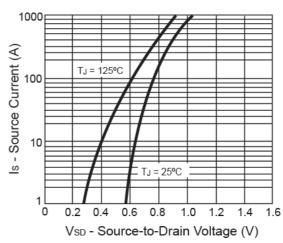
Gate Charge



#### **On-Resistance vs. Junction Temperature**



Source-Drain Diode Forward Voltage



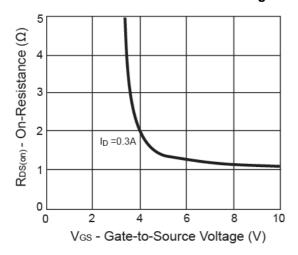


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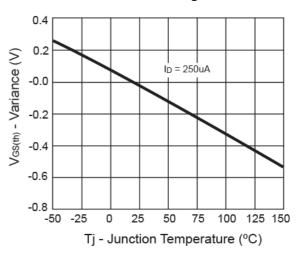


## **Electrical Characteristics Curve** (Ta = 25°C, unless otherwise noted)

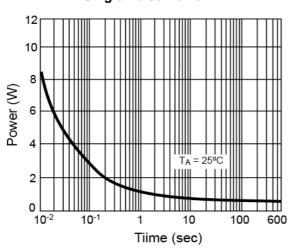
## On-Resistance vs. Gate-Source Voltage



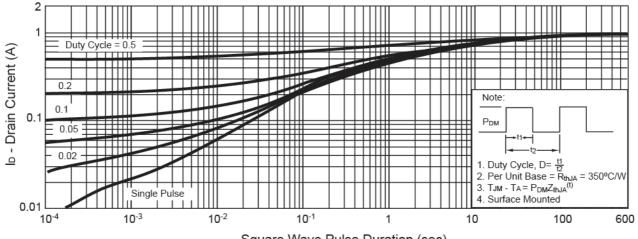
## Threshold Voltage



## **Single Pulse Power**



## Normalized Thermal Transient Impedance, Junction-to-Ambient



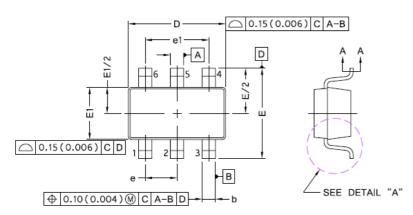
Square Wave Pulse Duration (sec)

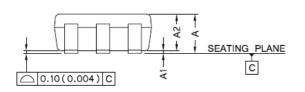


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# **SOT-363 Mechanical Drawing**





SOT-363 DIMENSION					
DIM	MILLIMETERS		INCHES		
DIIVI	MIN	MAX	MIN	MAX.	
Α	0.80	1.10	0.031	0.043	
A1	0	0.10	0	0.004	
A2	0.80	1.00	0.031	0.040	
b	0.15	0.30	0.006	0.012	
b1	0.15	0.25	0.006	0.010	
С	0.08	0.22	0.003	0.009	
c1	0.08	0.20	0.003	0.008	
D	1.90	2.10	0.074	0.084	
Е	2.00	2.20	0.078	0.086	
E1	1.15	1.35	0.045	0.055	
е	0.65 BSC		0.025	0.025 BSC	
e1	1.30 BSC 0.05		0.051	BSC	
L	0.26	0.46	0.010	0.018	
θ	00	80	00	8º	
θ1	4º	10°	4º	10°	

Version: C12

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# TSM2N7002KD 60V N-Channel MOSFET

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